

FIG. 1

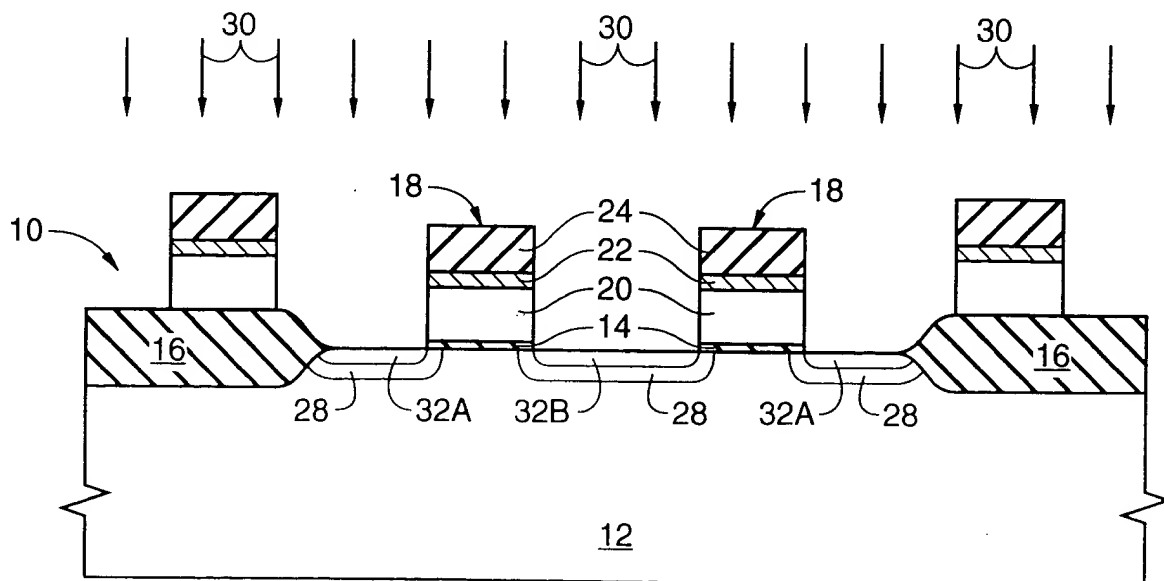


FIG. 2

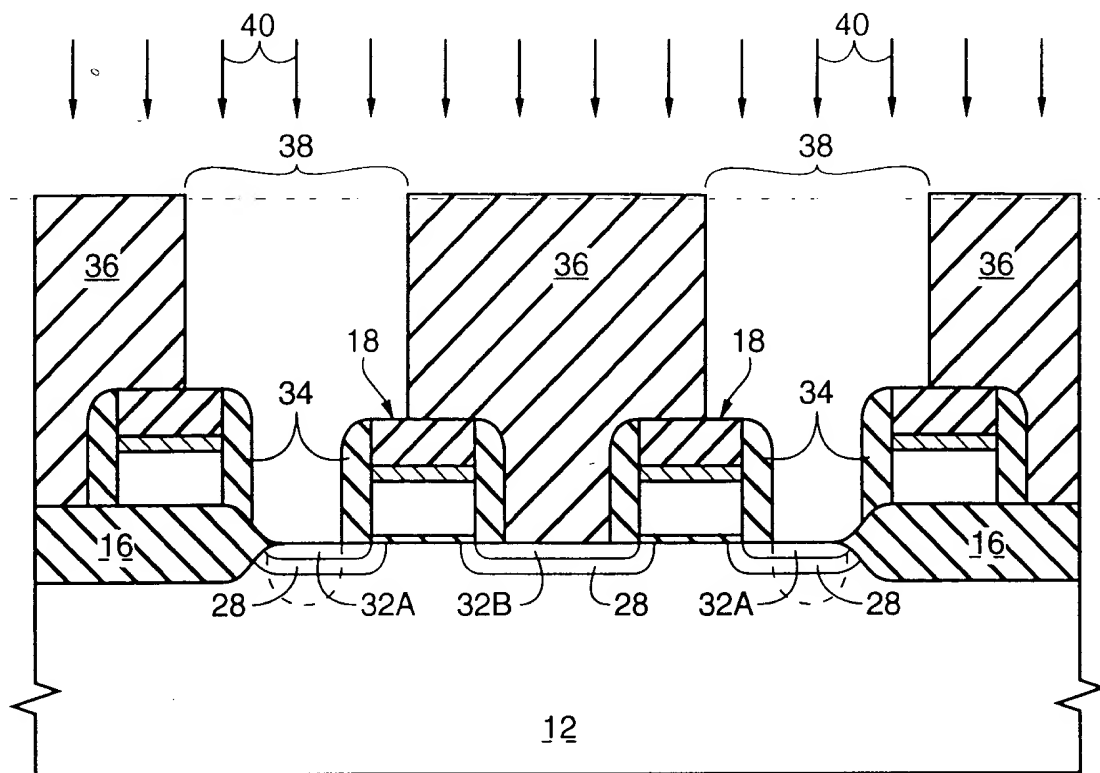


FIG. 3

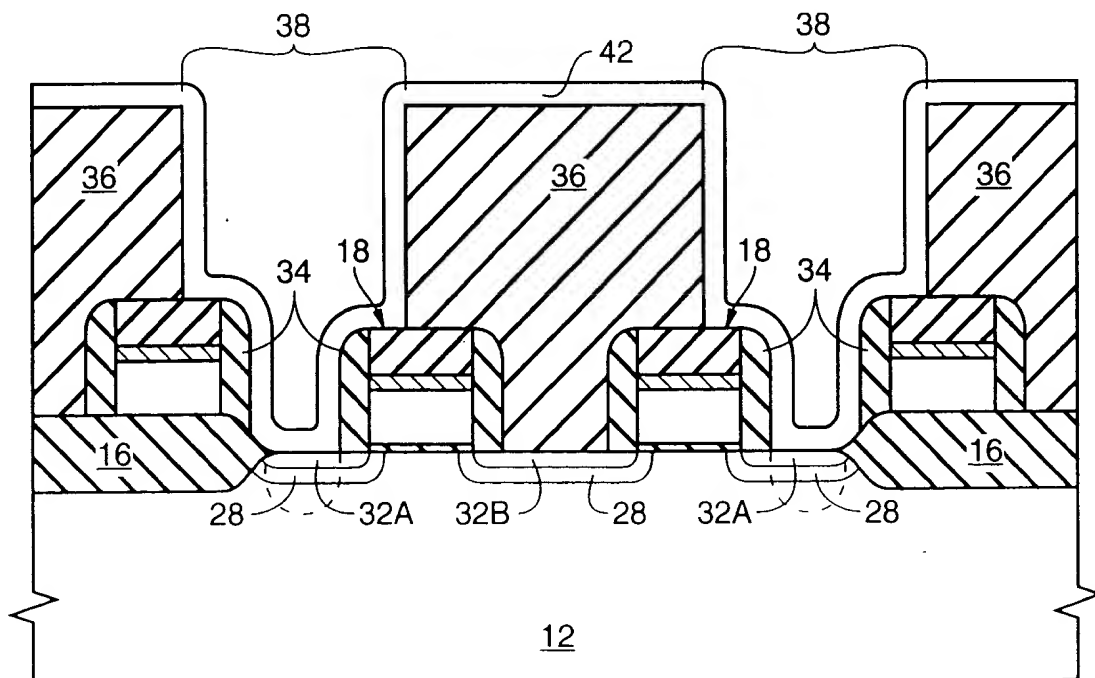


FIG. 4

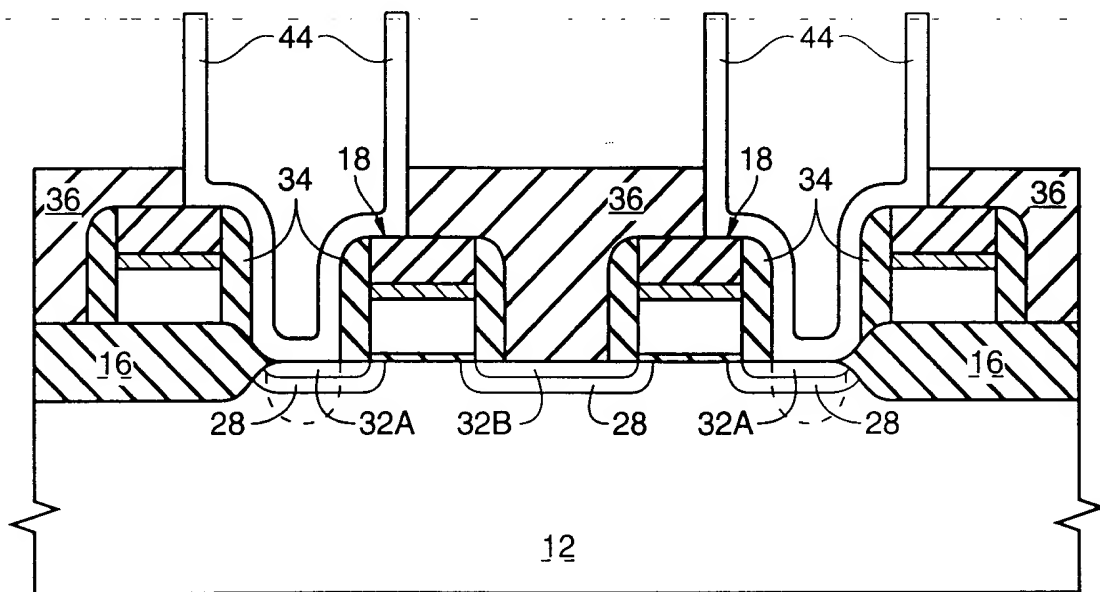


FIG. 5

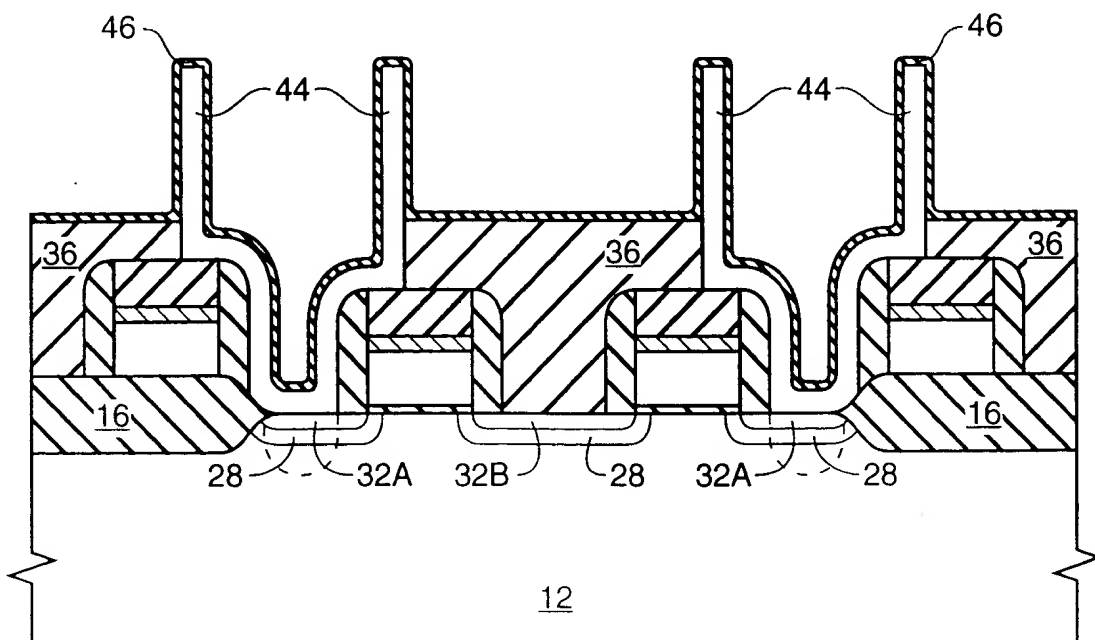


FIG. 6

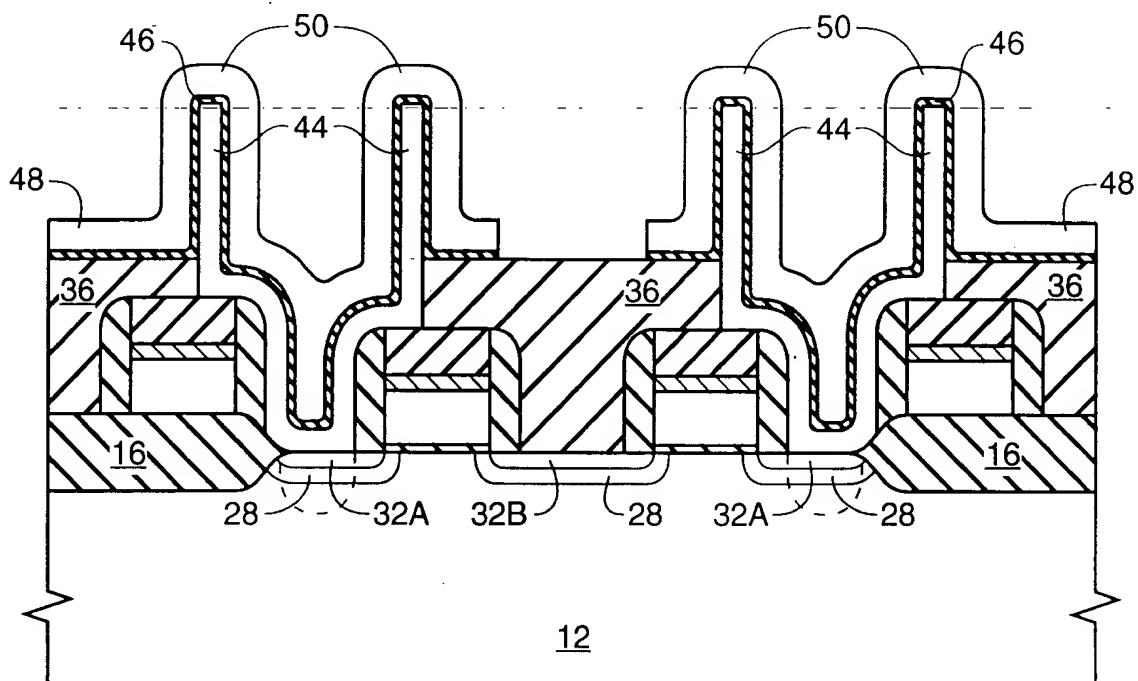


FIG. 7

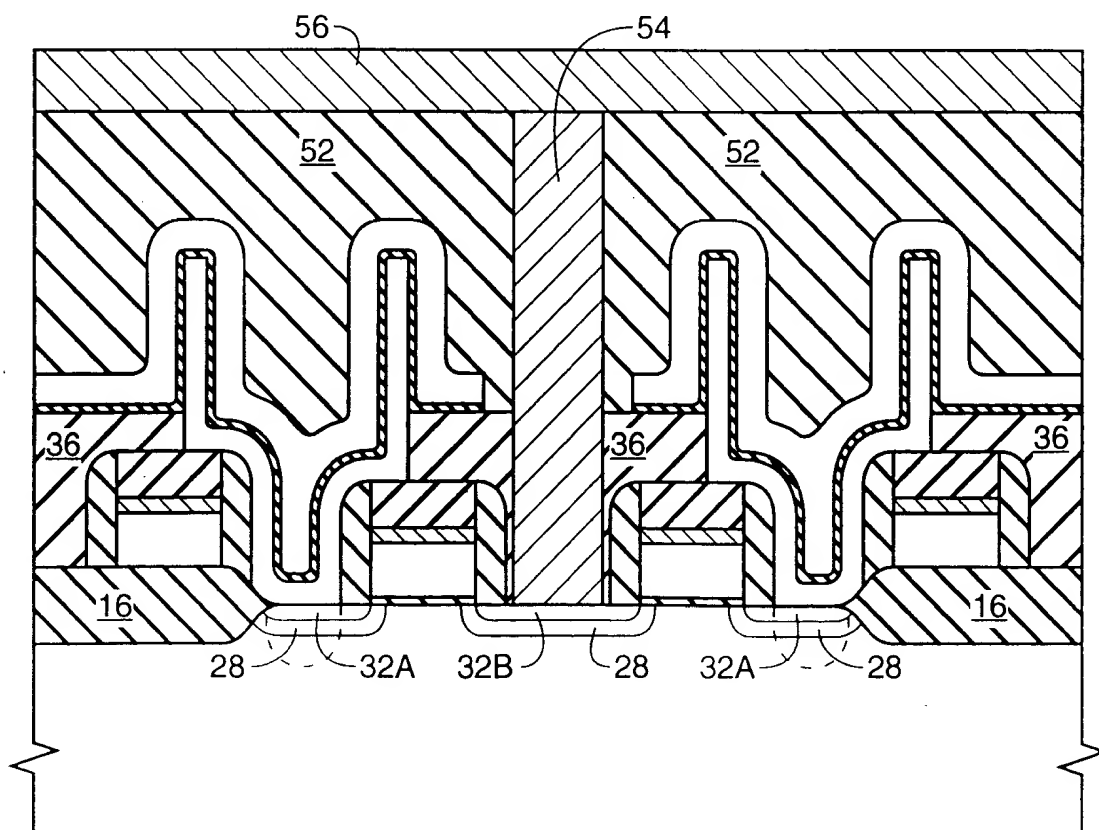


FIG. 8

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This diagram shows a cross-sectional view of a semiconductor device. A substrate 12 is at the base. A layer 16 is formed on the substrate. On top of layer 16, there is a periodic structure consisting of three rectangular blocks 18. Each block 18 is composed of a top layer 58 and a bottom layer 18. The blocks are separated by gaps 32A and 32B. The gaps 32A and 32B are filled with a material 28. The top surface of the blocks 18 is at a higher level than the top surface of the gaps 32A and 32B.

FIG. 10

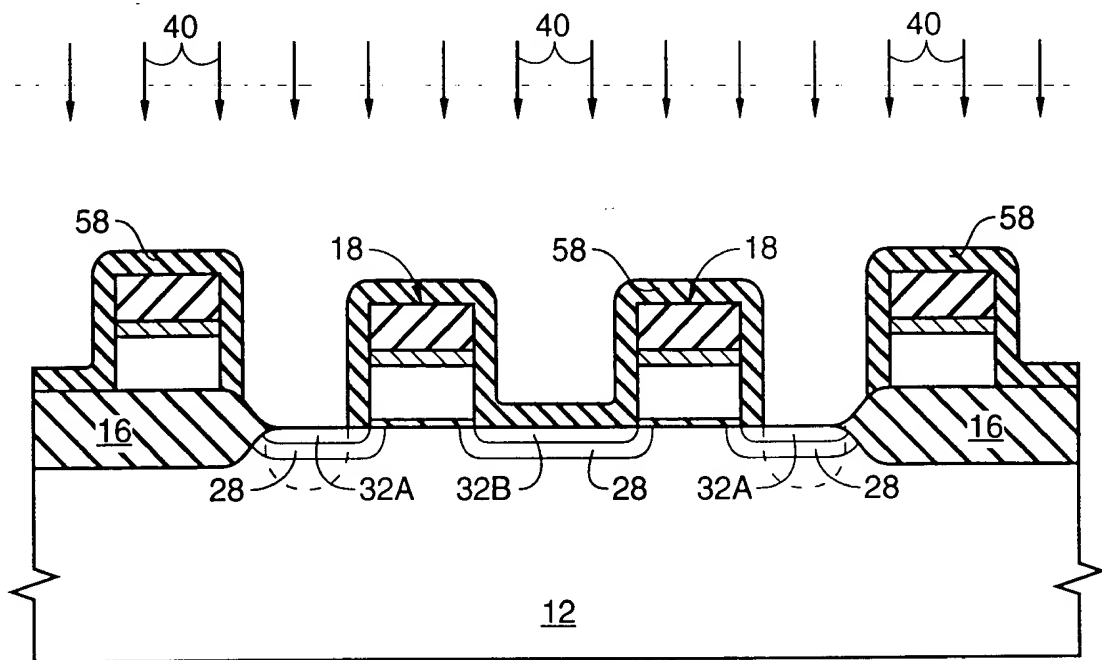


FIG. 11

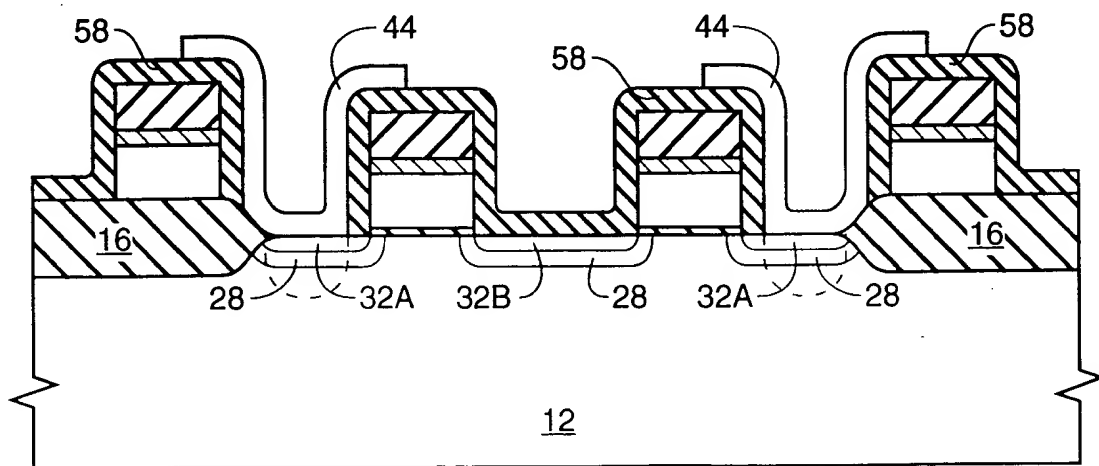


FIG. 12

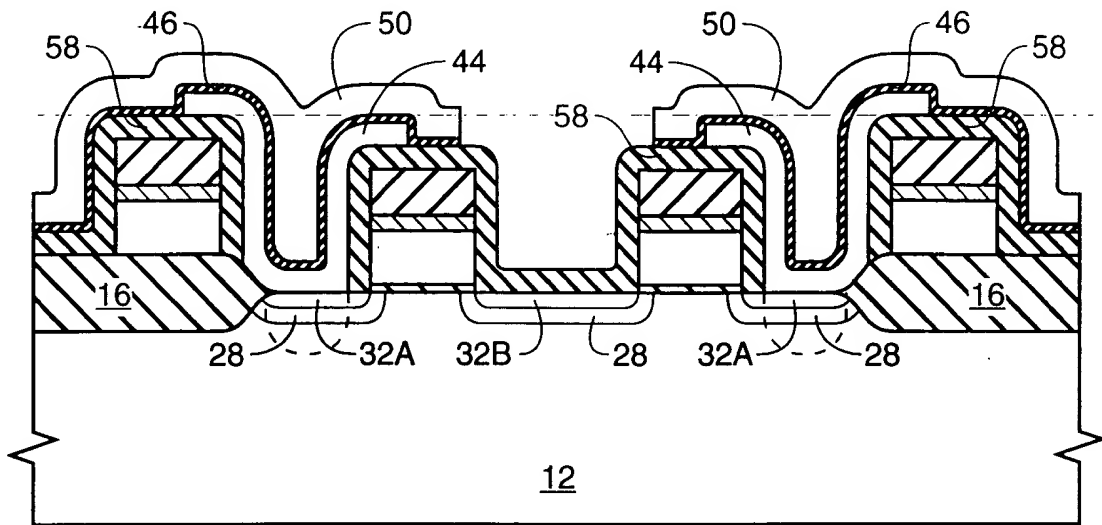


FIG. 13

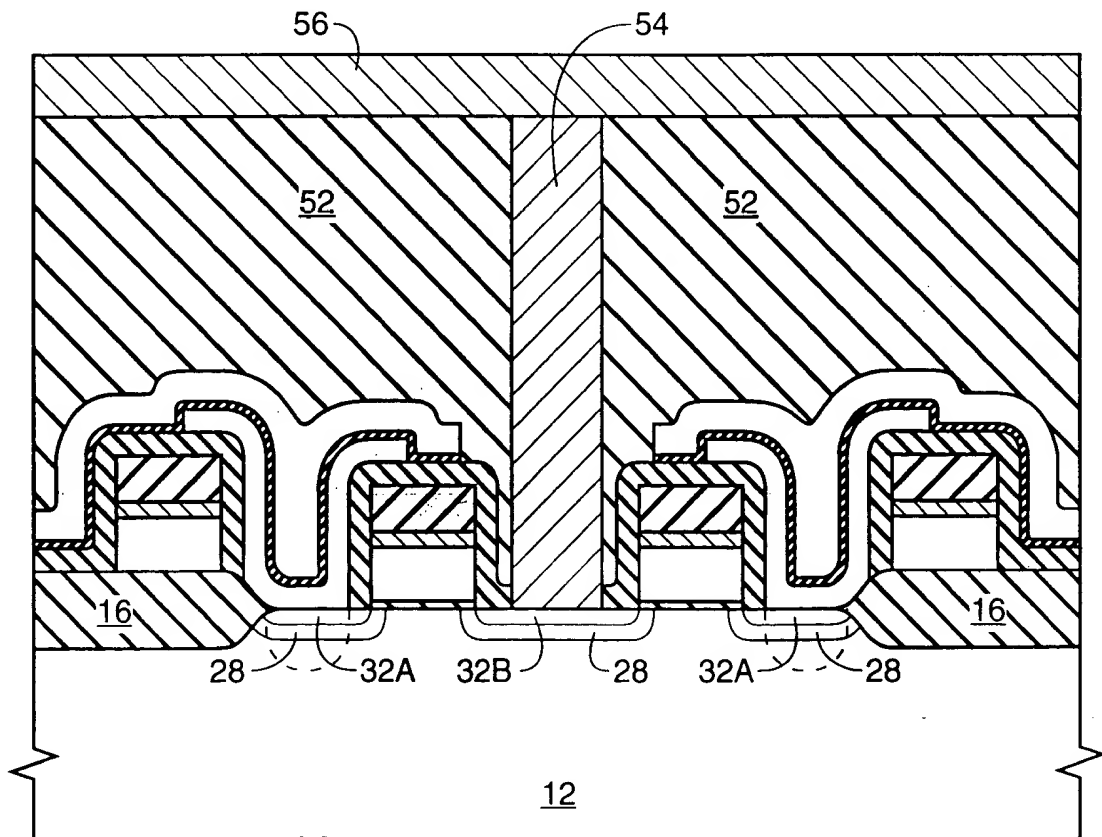


FIG. 14